

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

IN THE CLAIMS:

1. (Currently Amended): A process of removing residue from a complementary metal oxide semiconductor (CMOS) device which includes a tungsten gate conductor which has been subject to stack etch/ion implantations and photoresist stripping steps comprising the step of contacting a CMOS device which includes a tungsten gate conductor with a cleaning composition comprising sulfuric acid and hydrogen peroxide present in a volume ratio in the range of between of at least about 6:1[.] and about 10:1, said contact occurring at atmospheric pressure and a temperature of between about 70°C and about 90°C.

2-3 (Cancelled).

4. (Original): A process in accordance with Claim 1 wherein said volume ratio of sulfuric acid to hydrogen peroxide about 8:1.

5. (Original): A process in accordance with Claim 1 wherein contact of said composition with said CMOS device occurs over a period of between about 1 minute and about 10 minutes.

6. (Original): A process in accordance with Claim 5 wherein said period of time is in the range of between about 2 minutes and about 5 minutes.

7. (Original): A process in accordance with Claim 1 comprising pre-mixing of said sulfuric acid and said hydrogen peroxide whereby said cleaning composition is formed.

8. (Original): A process in accordance with Claim 1 comprising in-situ mixing of said sulfuric acid and said hydrogen peroxide whereby said cleaning composition is formed.

9. (Original): A process in accordance with Claim 1 wherein said cleaning composition consists essentially of sulfuric acid and hydrogen peroxide.

10. (Withdrawn): A composition which comprises sulfuric acid and hydrogen peroxide present in a volume ratio of at least about 6:1.

11. (Withdrawn): A composition in accordance with Claim 10 wherein said volume ratio is in the range of between 6:1 and about 100:1.

12. (Withdrawn): A composition in accordance with Claim 11 wherein said volume ratio is in the range of between about 6:1 and about 10:1.

13. (Withdrawn): A composition in accordance with Claim 12 wherein said volume ratio is about 8:1.

14. (Withdrawn): A composition which consists essentially of sulfuric acid and hydrogen peroxide present in a volume ratio of at least about 6:1.

15. (Withdrawn): A composition in accordance with Claim 14 wherein said volume ratio is in the range of between about 6:1 and about 100:1.

16. (Withdrawn): A composition in accordance with Claim 15 wherein said volume ratio is in the range of between about 6:1 and about 10:1.

17. (Withdrawn): A composition in accordance with Claim 16 wherein said volume ratio is about 8:1.